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Si Atomic Layer Epitaxy based on Si_2H_6 and Remote He Plasma Bombardment

by

A. Mahajan, J. Irby, D. Kinosky, R. Qian, S. Thomas, S. Banerjee, and A. Tasch
Department of Electrical and Computer Engineering
University of Texas at Austin
Austin, TX 78712

Tom Picraux
Sandia National Laboratories
Albuquerque, NM 87185

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A. Mahajan, J. Irby, D. Kinosky, R. Qian, S. Thomas, S. Banerjee, A. Tasch, and T. Picraux*

7. PERFORMING ORGANIZATION NAME(S) AND ADDRESS(ES)
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ECE Dept., 433 ENS
University of Texas at Austin
Austin, TX 78712

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13. ABSTRACT (Maximum 200 words)

Atomic layer Epitaxy(ALE) of silicon has been demonstrated by using remote helium plasma low energy bombardment to desorb H from a H-passivated Si(100) surface at low temperatures and subsequently chemisorbing disilane on the surface in a self-limiting fashion in a Remote Plasma Chemical Vapor Deposition(RPCVD) system in which the substrate is downstream from an r-f noble gas(He or Ar) glow discharge in order to minimize plasma damage. It was found necessary to desorb the H from the Si surface to create adsorption sites for Si bearing species such as Si_2H_6. Optimal He bombardment parameters were determined to be 30 W at 100 mTorr He at 400°C for 1-3 min. Helium was found to be more effective than Ar bombardment because of the closer match of the He and H masses compared to that between Ar and H. Monte Carlo TRIM simulations of He and Ar bombardment of H-terminated Si surfaces were performed to validate this hypothesis and to predict that approximately 3 r
H atoms are displaced by the incident He atoms, with no Si atom displacement for the He energies in the range of 15-60
Alternate Si_2H_6 dosing and He low energy bombardment cycles (~100-200) were performed to confirm ALE-mode o
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Silicon Atomic Layer Epitaxy Based on Disilane and Remote Helium Plasma Bombardment

A.Mahajan, J.Irby, D.Kinosky, R.Qian, S.Thomas, S.Banerjee, A.Tasch and T.Picraux*.
Department of ECE, University of Texas at Austin, Austin TX 78712.
***Sandia National Laboratories, Albuquerque NM.**

FAX: (512)-471-8575.

Atomic layer Epitaxy(ALE) of silicon has been demonstrated by using remote helium plasma low energy bombardment to desorb H from a H-passivated Si(100) surface at low temperatures and subsequently chemisorbing disilane on the surface in a self-limiting fashion. Silicon substrates were prepared using an RCA clean followed by a dilute HF dip to provide a clean, dihydride-terminated (1x1) surface, and were loaded into a Remote Plasma Chemical Vapor Deposition(RPCVD) system in which the substrate is downstream from an r-f noble gas(He or Ar) glow discharge in order to minimize plasma damage. An *in situ* remote H plasma clean at 250°C for 45 min. was used to remove O and C and provide an alternating monohydride and dihydride termination as evidenced by a 3x1 RHEED pattern. It was found necessary to desorb the H from the Si surface to create adsorption sites for Si bearing species such as Si_2H_6. Remote He plasma bombardment for 1-4 min. was investigated over a range of temperatures (250°C-410°C), pressures (50-400 mTorr) and r-f powers (6-30 W) in order to desorb the H and convert the (3x1) RHEED pattern to a (2x1) pattern which is characteristic of either a monohydride termination or a bare Si surface. It was found that as He pressures and r-f powers were raised the plasma potential and mean free paths were reduced, leading to lower He bombardment energies but higher fluxes. Optimal He bombardment parameters were determined to be 30 W at 100 mTorr He at 400°C for 1-3 min. Helium was found to be more effective than Ar bombardment because of the closer match of the He and H masses compared to that between Ar and H. Monte Carlo TRIM simulations of He and Ar bombardment of H-terminated Si surfaces were performed to validate this hypothesis and to predict that approximately 3 surface H atoms are displaced by the incident He atoms, with no Si atom displacement for the He energies in the range of 15-60 eV. The He bombardment cycles were followed by Si_2H_6 dosing over a range of partial pressures (10^{-7} Torr to 1.67 mTorr), temperatures(250°C-400°C) and times(20 sec to 3 min.) without plasma excitation, because it is believed that Si_2H_6 can chemisorb in a self limiting fashion on a bare Si surface as 2 silyl(SiH_3) species, presumably leading to a H terminated surface once again. The Si_2H_6 dosing pressures and times corresponded to saturation dosing ($\sim 10^7$ Langmuirs). Alternate Si_2H_6 dosing and He low energy bombardment cycles (~100-200) were performed to confirm ALE-mode of growth. It was found that the growth per cycle saturates with long Si_2H_6 dosing at a level which increases with He bombardment time. At 400°C, for 2 min. He bombardment at 100 mTorr and 30 W, the growth per cycle saturates at ~ 0.15 monolayers/cycle, while for 3 min. He bombardment, the Si growth saturates at ~0.44 monolayers/cycle. This agrees with ALE growth per cycle achieved by Green et al. using UV photo-thermal assisted ALE and is consistent with the steric hindrance presented by adsorbates. It was also confirmed that the growth is achieved only by using alternate He bombardment and Si_2H_6 dosing. Helium bombardment alone for a comparable time (3 min. x100cycles) causes a negligible change of the Si film thickness(<5Å). Similarly, thermal growth using Si_2H_6 under these conditions for (3 min. x100 cycles) causes negligible deposition(<5Å). A novel controller designed to switch gases and the r-f power supply repetitively will also be discussed.